

## HIGH SPEED 4K x 8 CMOS PROM/RPROM

### KEY FEATURES

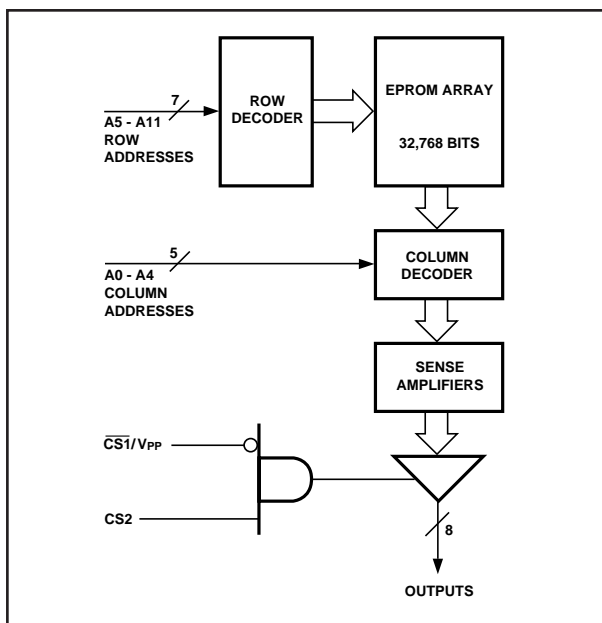
- **Ultra-Fast Access Time**
  - $t_{ACC} = 25 \text{ ns}$
  - $t_{CS} = 12 \text{ ns}$
- **Low Power Consumption**
- **Fast Programming**
- **Pin Compatible with 4K x 8 Bipolar PROMs**
- **Immune to Latch-UP**
  - Up to 200 mA
- **ESD Protection Exceeds 2000 V**
- **Available in 300 Mil DIP and PLDCC**

### GENERAL DESCRIPTION

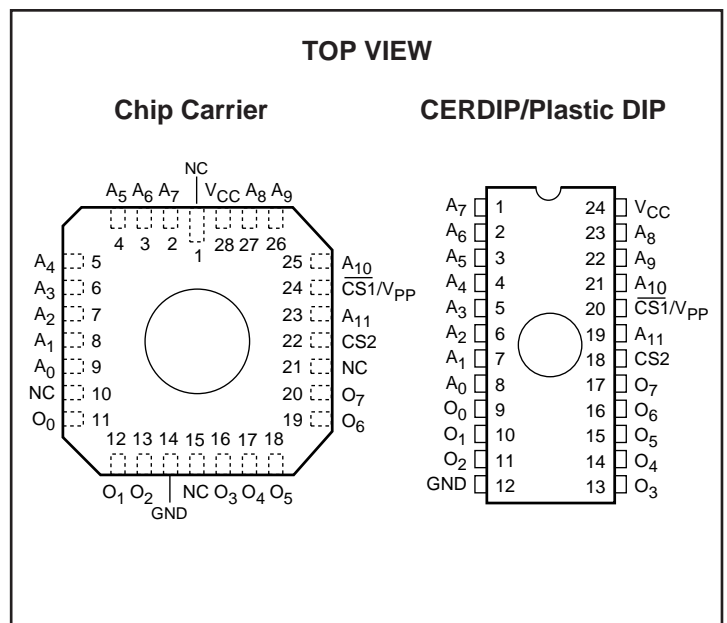
The WS57C43C is a High Performance 32K UV Erasable Electrically Re-Programmable Read Only Memory (RPROM). It is manufactured in an advanced CMOS technology which enables it to operate at Bipolar PROM speeds while consuming only 25% of the power required by its Bipolar counterparts. A further advantage of the WS57C43C over Bipolar PROM devices is the fact that it utilizes a proven EPROM technology. This enables the entire memory array to be tested for switching characteristics and functionality after assembly. Unlike devices which cannot be erased, every WS5743C in a windowed package is 100% tested with worst case test patterns both before and after assembly.

The WS57C43C is configured in the standard Bipolar PROM pinout which provides an easy upgrade path for systems which are currently using Bipolar PROMs, or its predecessor, the WS57C43B.

### BLOCK DIAGRAM



### PIN CONFIGURATION



### PRODUCT SELECTION GUIDE

PARAMETER	57C43C-25	57C43C-35	57C43C-45	57C43C-55	57C43C-70
Address Access Time (Max)	25 ns	35 ns	45 ns	55 ns	70 ns
CS to Output Valid Time (Max)	12 ns	20 ns	25 ns	25 ns	25 ns

**ABSOLUTE MAXIMUM RATINGS\***

Storage Temperature.....-65° to + 150°C  
 Voltage on any Pin with Respect to Ground .....-0.6V to +7V  
 $V_{PP}$  with Respect to Ground.....-0.6V to + 14V  
 ESD Protection.....>2000V

**\*NOTICE:**

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect device reliability.

**MODE SELECTION**

MODE \ PINS	$\overline{CS1}/V_{PP}$	CS2	$V_{CC}$	OUTPUTS
Read	$V_{IL}$	$V_{IH}$	$V_{CC}$	$D_{OUT}$
Output Disable	$V_{IH}$	X	$V_{CC}$	High Z
Output Disable	X	$V_{IL}$	$V_{CC}$	High Z
Program	$V_{PP}$	X	$V_{CC}$	$D_{IN}$
Program Verify	$V_{IL}$	$V_{IH}$	$V_{CC}$	$D_{OUT}$

**OPERATING RANGE**

RANGE	TEMPERATURE	$V_{CC}$
Commercial	0°C to +70°C	+5V ± 10%
Industrial	-40°C to +85°C	+5V ± 10%
Military	-55°C to +125°C	+5V ± 10%

**DC READ CHARACTERISTICS** Over Operating Range. (See Above)

SYMBOL	PARAMETER	TEST CONDITIONS	MIN	MAX	UNITS
$V_{IL}$	Input Low Voltage	(Note 3)	-0.1	0.8	V
$V_{IH}$	Input High Voltage	(Note 3)	2.0	$V_{CC} + 0.3$	V
$V_{OL}$	Output Low Voltage	$I_{OL} = 16$ mA		0.4	V
$V_{OH}$	Output High Voltage	$I_{OH} = -4$ mA	2.4		V
$I_{CC1}$	$V_{CC}$ Active Current (CMOS)	$V_{CC} = 5.5$ V, $f = 0$ MHz (Note 1), Output Not Loaded Add 3 mA/MHz for AC Operation	Comm'l	30	mA
			Industrial	35	mA
			Military	35	mA
$I_{CC2}$	$V_{CC}$ Active Current (TTL)	$V_{CC} = 5.5$ V, $f = 0$ MHz (Note 1), Output Not Loaded Add 3 mA/MHz for AC Operation	Comm'l	40	mA
			Industrial	50	mA
			Military	50	mA
$I_{LI}$	Input Leakage Current	$V_{IN} = 5.5$ V or Gnd	-10	10	µA
$I_{LO}$	Output Leakage Current	$V_{OUT} = 5.5$ V or Gnd	-10	10	µA

- NOTES:**
1. CMOS inputs:  $GND \pm 0.3V$  or  $V_{CC} \pm 0.3V$ .
  2. TTL inputs:  $V_{IL} \leq 0.8V$ ,  $V_{IH} \geq 2.0V$ .
  3. These are absolute voltages with respect to device ground pin and include all overshoots due to system and/or tester noise. Do not attempt to test these values without suitable equipment.

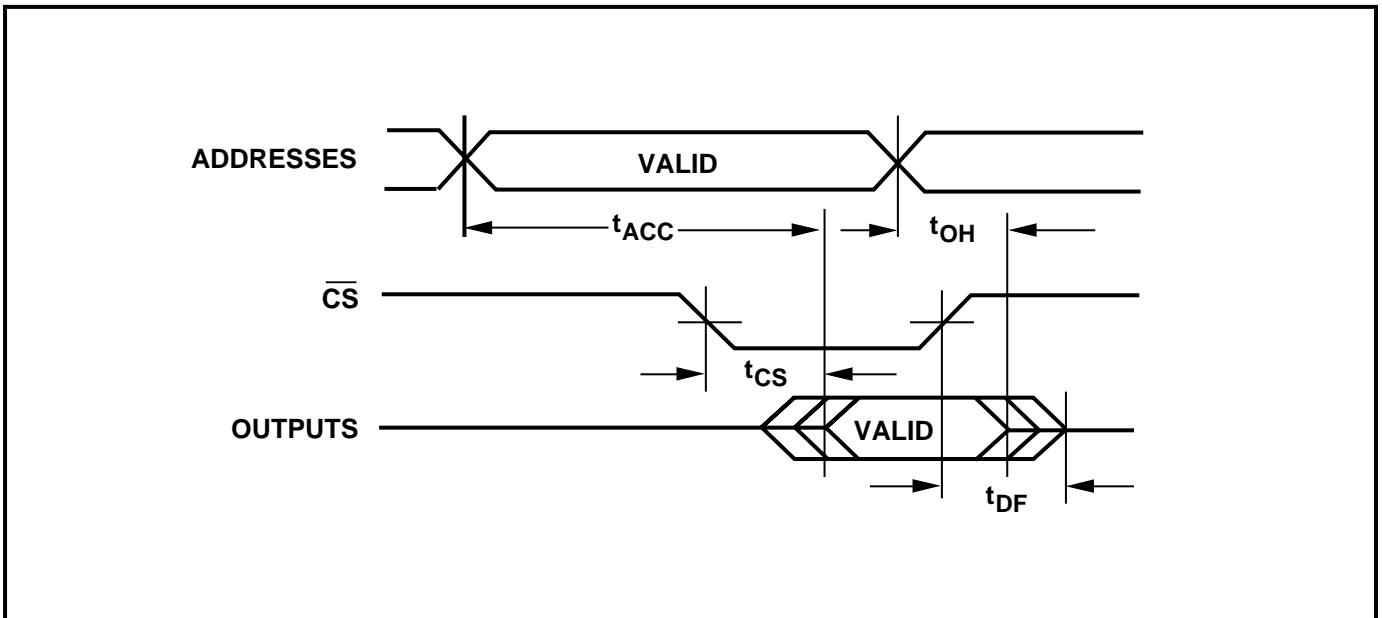


**AC READ CHARACTERISTICS** Over Operating Range. (See Above)

PARAMETER	SYMBOL	57C43C-25		57C43C-35		57C43C-45		57C43C-55		57C43C-70		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
Address to Output Delay	$t_{ACC}$		25		35		45		55		70	ns
$\overline{CS1}$ to Output Delay	$t_{CS}$		12		20		25		25		25	
Output Disable to Output Float*	$t_{DF}$		12		25		25		25		25	
Address to Output Hold	$t_{OH}$	0		0		0		0		0		

\*Sampled, Not 100% Tested.

**AC READ TIMING DIAGRAM**



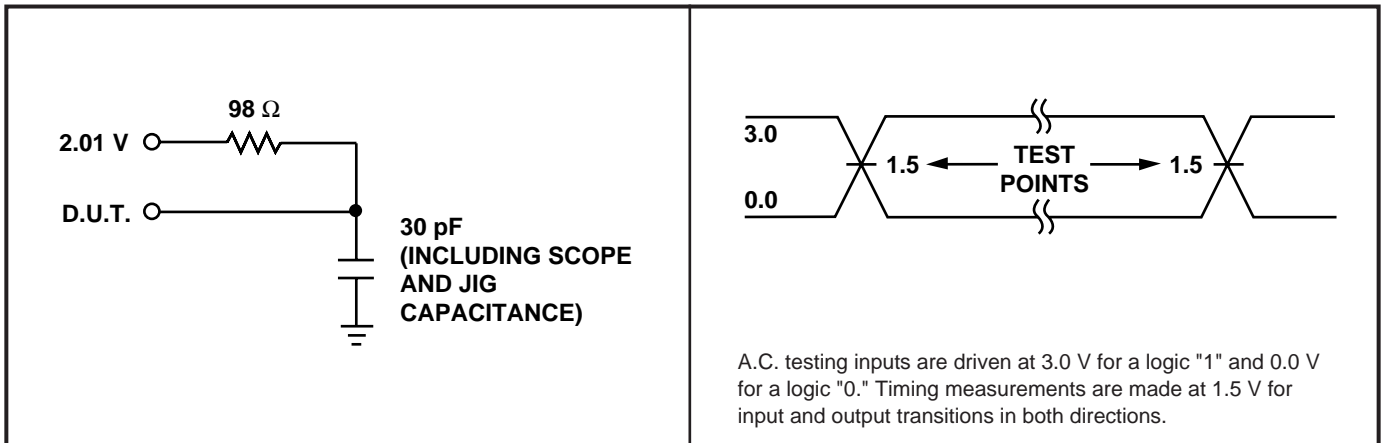
**CAPACITANCE**<sup>(4)</sup>  $T_A = 25^\circ\text{C}$ ,  $f = 1\text{ MHz}$

SYMBOL	PARAMETER	CONDITIONS	TYP <sup>(5)</sup>	MAX	UNITS
$C_{IN}$	Input Capacitance	$V_{IN} = 0\text{V}$	4	6	pF
$C_{OUT}$	Output Capacitance	$V_{OUT} = 0\text{V}$	8	12	pF
$C_{VPP}$	$V_{PP}$ Capacitance	$V_{PP} = 0\text{V}$	18	25	pF

**NOTES:** 4. This parameter is only sampled and is not 100% tested.  
 5. Typical values are for  $T_A = 25^\circ\text{C}$  and nominal supply voltages.

**TEST LOAD** (High Impedance Test Systems)

**A.C. TESTING INPUT/OUTPUT WAVEFORM**



**NOTE:** 6. Provide adequate decoupling capacitance as close as possible to this device to achieve the published A.C. and D.C. parameters. A 0.1 microfarad capacitor in parallel with a 0.01 microfarad capacitor connected between  $V_{CC}$  and ground is recommended. Inadequate decoupling may result in access time degradation or other transient performance failures.



**NORMALIZED SUPPLY CURRENT  
vs.  
SUPPLY VOLTAGE**



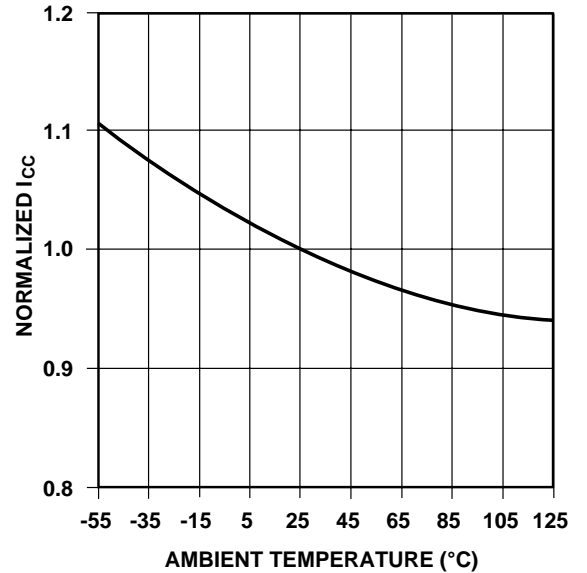
**TYPICAL ACCESS TIME CHANGE  
vs.  
OUTPUT LOADING**



**NORMALIZED T<sub>aa</sub>  
vs.  
AMBIENT TEMPERATURE**



**NORMALIZED SUPPLY CURRENT  
vs.  
AMBIENT TEMPERATURE**



**PROGRAMMING INFORMATION**

**DC CHARACTERISTICS** ( $T_A = 25 \pm 5^\circ\text{C}$ ,  $V_{CC} = 6.25 \text{ V} \pm 0.25 \text{ V}$ ,  $V_{PP} = 12.75 \pm 0.25 \text{ V}$ )

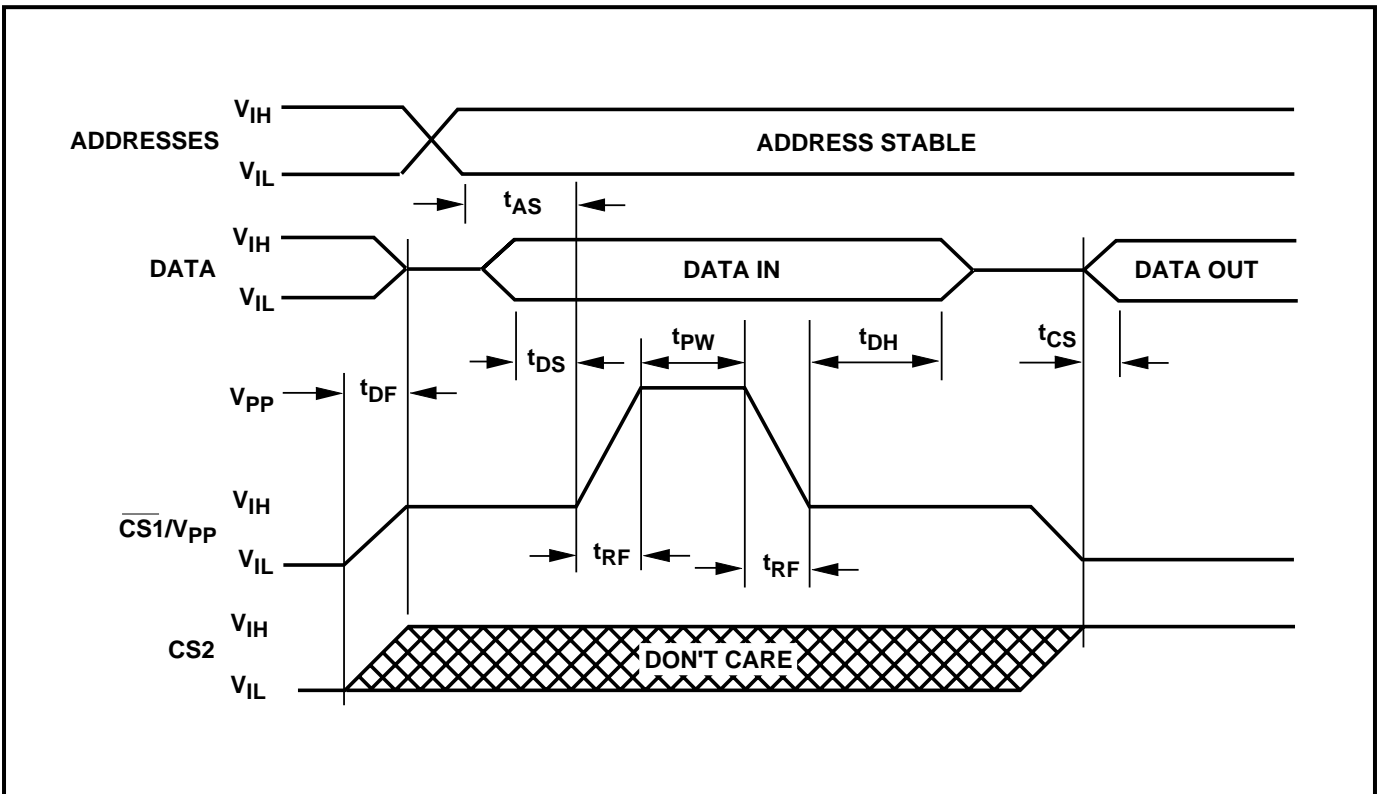
SYMBOLS	PARAMETER	MIN	MAX	UNITS
$I_{LI}$	Input Leakage Current ( $V_{IN} = V_{CC}$ or Gnd)	-10	10	$\mu\text{A}$
$I_{PP}$	$V_{PP}$ Supply Current During Programming Pulse		60	mA
$I_{CC}$	$V_{CC}$ Supply Current		30	mA
$V_{OL}$	Output Low Voltage During Verify ( $I_{OL} = 16 \text{ mA}$ )		0.45	V
$V_{OH}$	Output High Voltage During Verify ( $I_{OH} = -4 \text{ mA}$ )	2.4		V

NOTES: 8.  $V_{PP}$  must not be greater than 13 volts including overshoot.

**AC CHARACTERISTICS** ( $T_A = 25 \pm 5^\circ\text{C}$ ,  $V_{CC} = 6.25 \text{ V} \pm 0.25 \text{ V}$ ,  $V_{PP} = 12.75 \pm 0.25 \text{ V}$ )

SYMBOLS	PARAMETER	MIN	TYP	MAX	UNITS
$t_{AS}$	Address Setup Time	2			$\mu\text{s}$
$t_{DF}$	Chip Disable Setup Time			30	ns
$t_{DS}$	Data Setup Time	2			$\mu\text{s}$
$t_{PW}$	Program Pulse Width	100		200	$\mu\text{s}$
$t_{DH}$	Data Hold Time	2			$\mu\text{s}$
$t_{CS}$	Chip Select Delay			30	ns
$t_{RF}$	$V_{PP}$ Rise and Fall Time	1			$\mu\text{s}$

**PROGRAMMING WAVEFORM**



**ORDERING INFORMATION**

PART NUMBER	SPEED (ns)	PACKAGE TYPE	PACKAGE DRAWING	OPERATING TEMPERATURE RANGE	WSI MANUFACTURING PROCEDURE
WS57C43C-25D	25	24 Pin CERDIP, 0.6"	D1	Comm'l	Standard
WS57C43C-25J	25	28 Pin PLDCC	J3	Comm'l	Standard
WS57C43C-25S	25	24 Pin Plastic DIP, 0.3"	S1	Comm'l	Standard
WS57C43C-25T	25	24 Pin CERDIP, 0.3"	T1	Comm'l	Standard
WS57C43C-35CMB*	35	28 Pad CLLCC, 0.3"	C1	Military	MIL-STD-883C
WS57C43C-35D	35	24 Pin CERDIP, 0.6"	D1	Comm'l	Standard
WS57C43C-35J	35	28 Pin PLDCC	J3	Comm'l	Standard
WS57C43C-35JI	35	28 Pin PLDCC	J3	Industrial	Standard
WS57C43C-35S	35	24 Pin Plastic DIP, 0.3"	S1	Comm'l	Standard
WS57C43C-35T	35	24 Pin CERDIP, 0.3"	T1	Comm'l	Standard
WS57C43C-35TMB*	35	24 Pin CERDIP, 0.3"	T1	Military	MIL-STD-883C
WS57C43C-45D	45	24 Pin CERDIP, 0.6"	D1	Comm'l	Standard
WS57C43C-45J	45	28 Pin PLDCC	J3	Comm'l	Standard
WS57C43C-45JI	45	28 Pin PLDCC	J3	Industrial	Standard
WS57C43C-45S	45	24 Pin Plastic DIP, 0.3"	S1	Comm'l	Standard
WS57C43C-45T	45	24 Pin CERDIP, 0.3"	T1	Comm'l	Standard
WS57C43C-45TI	45	24 Pin CERDIP, 0.3"	T1	Industrial	Standard
WS57C43C-45TMB*	45	24 Pin CERDIP, 0.3"	T1	Military	MIL-STD-883C
WS57C43C-55D	55	24 Pin CERDIP, 0.6"	D1	Comm'l	Standard
WS57C43C-55T	55	24 Pin CERDIP, 0.3"	T1	Comm'l	Standard
WS57C43C-55TMB*	55	24 Pin CERDIP, 0.3"	T1	Military	MIL-STD-883C
WS57C43C-70D	70	24 Pin CERDIP, 0.6"	D1	Comm'l	Standard

**NOTE:** The actual part marking will not include the initials "WS."

\*SMD product. See section 4 for DESC SMD numbers.

**PROGRAMMING/ALGORITHMS/ERASURE/PROGRAMMERS**

**REFER TO PAGE 5-1**

The WS57C43C is programmed using Algorithm D shown on page 5-9.

